## Hangyang Chen

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/5482497/publications.pdf

Version: 2024-02-01

11	129	1684188	1281871 11
papers	citations	h-index	g-index
11 all docs	11 docs citations	11 times ranked	195 citing authors

#	Article	IF	CITATIONS
1	High density GaN/AlN quantum dots for deep UV LED with high quantum efficiency and temperature stability. Scientific Reports, 2014, 4, 5166.	3.3	38
2	Improved Characteristics of AlGaN-Based Deep Ultraviolet Light-Emitting Diodes with Superlattice p-Type Doping. IEEE Photonics Journal, 2017, 9, 1-7.	2.0	21
3	Enhancement of p-type conductivity by modifying the internal electric field in Mg- and Si-Î-codoped AlxGa1â^'xN/AlyGa1â^'yN superlattices. Applied Physics Letters, 2009, 95, .	3.3	19
4	Integral Monolayer-Scale Featured Digital-Alloyed AlN/GaN Superlattices Using Hierarchical Growth Units. Crystal Growth and Design, 2019, 19, 1720-1727.	3.0	19
5	Vacuum Rabi Splitting of Exciton–Polariton Emission in an AlN Film. Scientific Reports, 2013, 3, 3551.	3.3	10
6	Symmetrically abrupt GaN/AlGaN superlattices by alternative interface–interruption scheme. Journal of Materials Research, 2013, 28, 716-722.	2.6	6
7	Control of two-dimensional growth of AlN and high Al-content AlGaN-based MQWs for deep-UV LEDs. AIP Advances, 2013, 3, 052103.	1.3	5
8	Origins and suppressions of parasitic emissions in ultraviolet light-emitting diode structures. Journal of Materials Research, 2010, 25, 1037-1040.	2.6	4
9	Structural properties of InN films grown in different conditions by metalorganic vapor phase epitaxy. Journal of Materials Research, 2011, 26, 775-780.	2.6	4
10	Modification of strain and optical polarization property in AlGaN multiple quantum wells by introducing ultrathin AlN layer. AlP Advances, 2019, 9, .	1.3	2
11	Regulating the Valence Level Arrangement of High-Al-content AlGaN Quantum Wells Using Additional Potentials with Mg Doping. Physical Chemistry Chemical Physics, 2022, , .	2.8	1